MBR1535CT, MBR1545CT

SWITCHMODE™ Power Rectifier

Features and Benefits

- Center−Tap Configuration
- Low Forward Voltage
- Low Power Loss / High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 15 A Total (7.5 A Per Diode Leg)
- Pb−Free Package is Available*

Applications

- Power Supply − Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

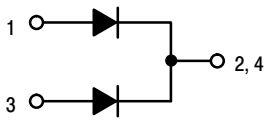
- Case: Epoxy, Molded
- Epoxy Meets UL 94, V−0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model = 3B
  Machine Model = C

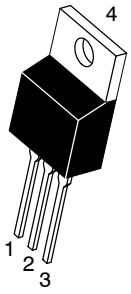
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor®

http://onsemi.com

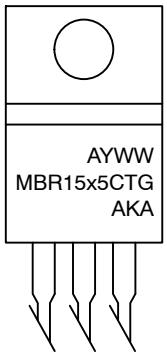
SCHOTTKY BARRIER RECTIFIERS 15 AMPERES 35 and 45 VOLTS





TO−220AB CASE 221A PLASTIC

MARKING DIAGRAM



A	= Assembly Location
Y	= Year
WW	= Work Week
x	= 3 or 4
G	= Pb−Free Package
AKA	= Diode Polarity

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBR1535CT MBR1545CT	V_{RRM} V_{RWM} V_R	 35 45	V
Average Rectified Forward Current (T_C = 163°C) Per Diode Per Device	$I_{F(AV)}$	 7.5 15	A
Peak Repetitive Forward Current (Square Wave, 20 kHz, T_C = 161°C) Per Diode	I_{FRM}	15	A
Non−Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	150	A
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I_{RRM}	1.0	A
Storage Temperature Range	T_{stg}	−65 to +175	°C
Operating Junction Temperature (Note 1)	T_J	−65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	V/μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS PER DIODE

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction−to−Case (Min. Pad)	$R_{\theta JC}$	3.0	°C/W
Maximum Thermal Resistance, Junction−to−Ambient (Min. Pad)	$R_{\theta JA}$	60	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE

Characteristic	Symbol	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) (i_F = 7.5 Amps, T_J = 125°C) (i_F = 15 Amps, T_J = 125°C) (i_F = 15 Amps, T_J = 25°C)	v_F	 − − −	 0.47 0.63 0.66	 0.57 0.72 0.84	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, T_J = 125°C) (Rated DC Voltage, T_J = 25°C)	i_R	 − −	 10 0.025	 15 0.1	mA

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

ORDERING INFORMATION

Device	Package	Shipping†
MBR1535CT	TO−220	50 Units / Rail
MBR1535CTG	TO−220 (Pb−Free)	50 Units / Rail
MBR1545CT	TO−220	50 Units / Rail
MBR1545CTG	TO−220 (Pb−Free)	50 Units / Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

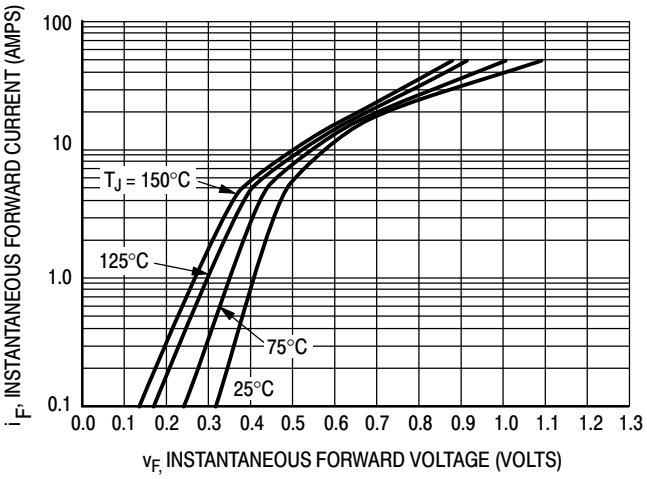


Figure 1. Typical Forward Voltage

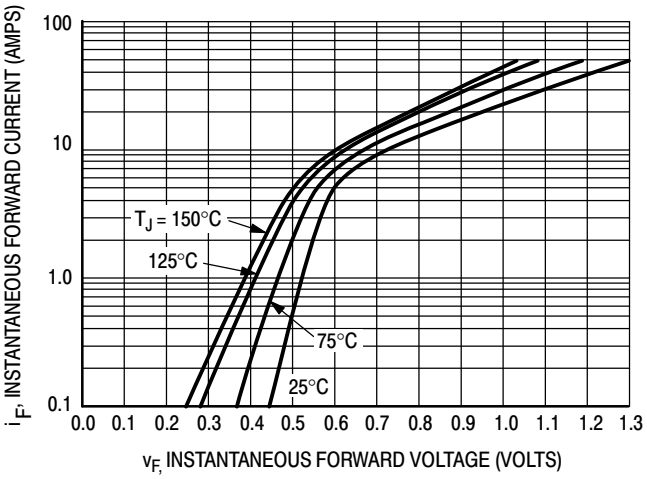


Figure 2. Maximum Forward Voltage

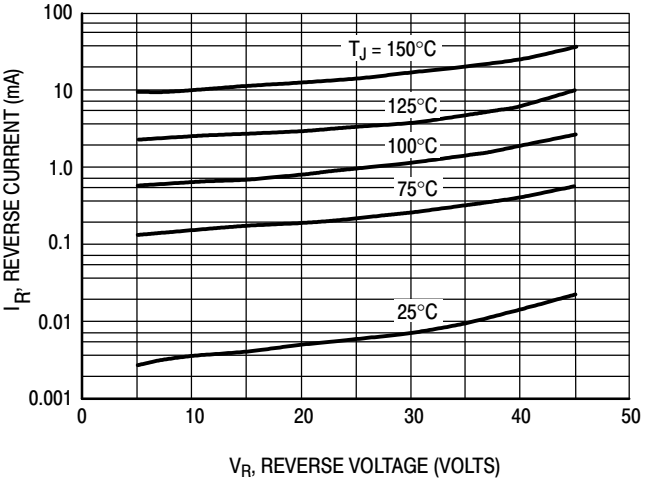


Figure 3. Typical Reverse Current

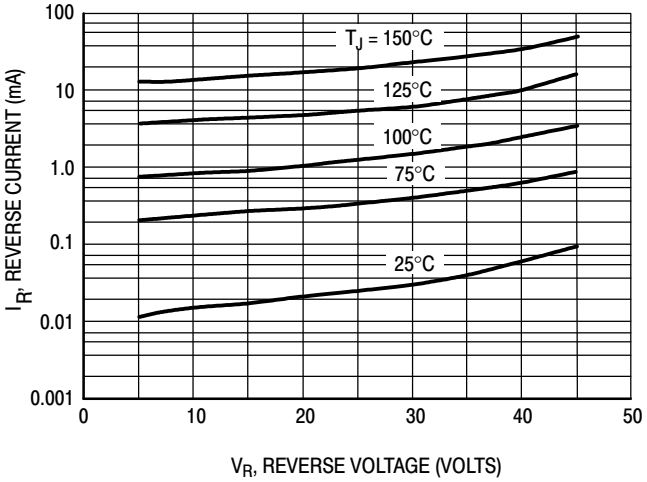


Figure 4. Maximum Reverse Current

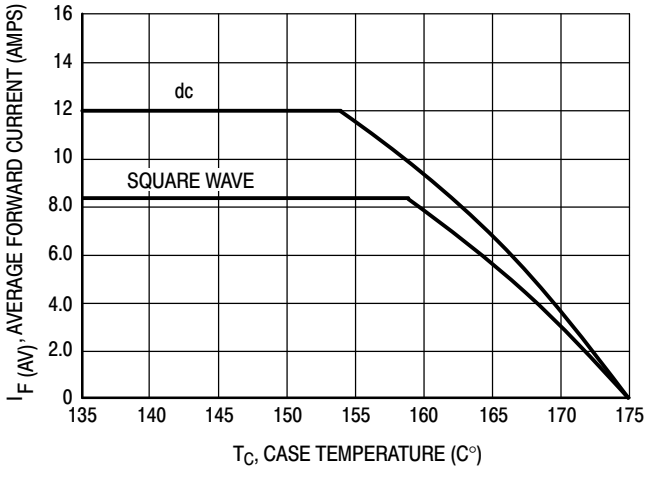


Figure 5. Current Derating, Case Per Leg

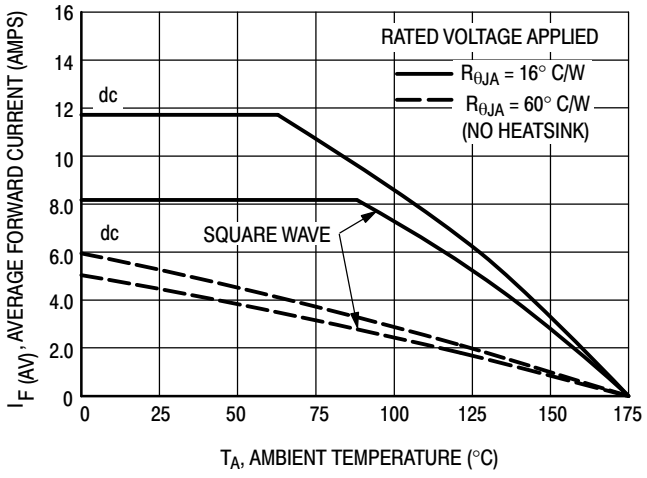


Figure 6. Current Derating, Ambient Per Leg

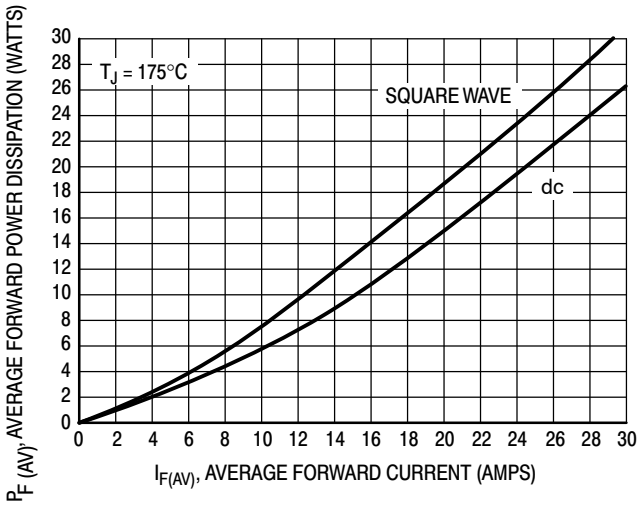


Figure 7. Forward Power Dissipation

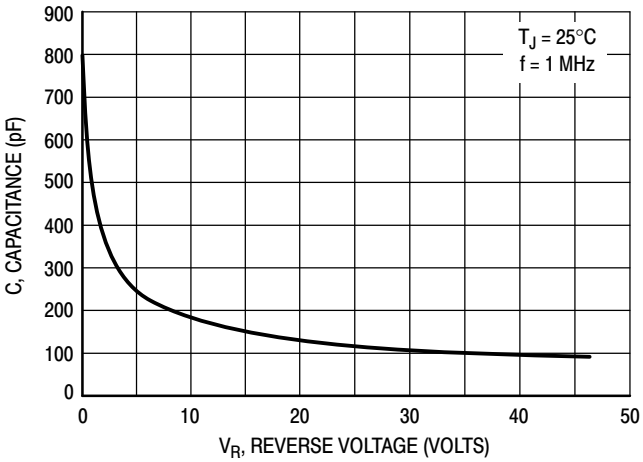
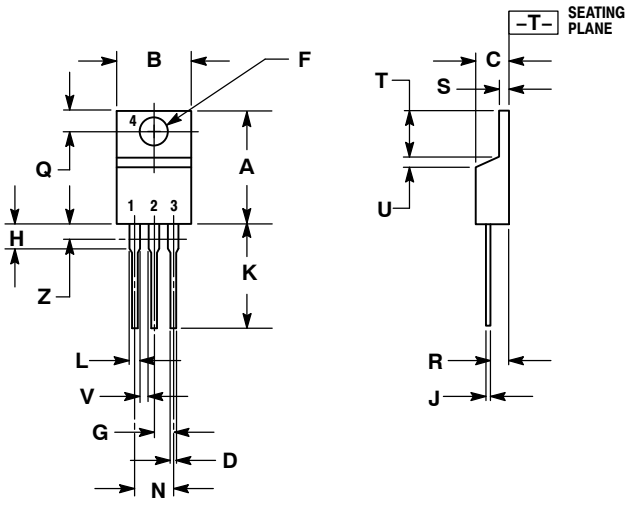


Figure 8. Typical Capacitance

PACKAGE DIMENSIONS

TO−220
CASE 221A−09
ISSUE AF



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
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ON Semiconductor Website: **www.onsemi.com**

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For additional information, please contact your local Sales Representative

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